

MA4X159A (MA159A)

Silicon epitaxial planar type

For switching circuits

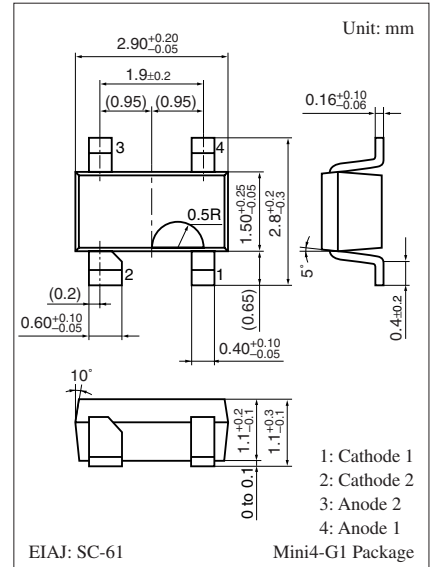
■ Features

- Two isolated elements contained in one package, allowing high-density mounting
- Short reverse recovery time t_{rr}
- Small terminal capacitance C_t

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

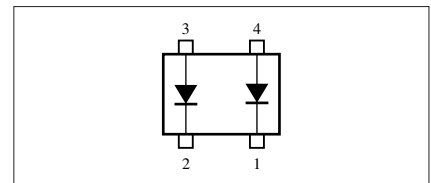
Parameter	Symbol	Rating	Unit
Reverse voltage	V_R	80	V
Maximum peak reverse voltage	V_{RM}	80	V
Forward current	Single	100	mA
	Double	75	
Peak forward current	Single	225	mA
	Double	170	
Non-repetitive peak forward surge current *	Single	500	mA
	Double	375	
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Note) *: $t = 1 \text{ s}$



Marking Symbol: M1B

Internal Connection



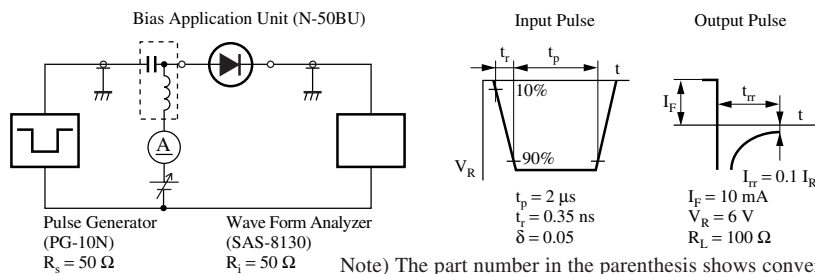
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	V_F	$I_F = 100 \text{ mA}$		0.95	1.20	V
Reverse voltage	V_R	$I_R = 100 \mu\text{A}$	80			V
Reverse current	I_R	$V_R = 75 \text{ V}$			100	nA
Terminal capacitance	C_t	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$		0.9	2.0	pF
Reverse recovery time *	t_{rr}	$I_F = 10 \text{ mA}, V_R = 6 \text{ V}$ $I_{rr} = 0.1 I_R, R_L = 100 \Omega$			3	ns

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 measuring methods for diodes.

2. Absolute frequency of input and output is 100 MHz.

3. *: t_{rr} measurement circuit



Note) The part number in the parenthesis shows conventional part number.

